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Docket No.: M4065.0319/P319-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Ronald A. Weimer, et al.

Application No.: 09/912,558

Group Art Unit: 2813

Filed: July 26, 2001

Examiner: Erik J. Kielin

For: FABRICATION OF DRAM AND OTHER  
SEMICONDUCTOR DEVICES WITH AN  
INSULATING FILM USING A WET RAPID  
THERMAL OXIDATION PROCESS

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AMENDMENT

**BOX: Non-Fee Amendment**  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated October 7, 2002 rejecting claims 13, 14, 16, 17, and 41-42, please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please rewrite claim 41 as follows:

Sub  
F2  
E1

41. (twice amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film with a thickness greater than about 40 Angstroms over a semiconductor substrate; and

subjecting the dielectric film to a wet oxidation with steam in a rapid thermal